



IPW

Customer No. 31561
Docket No. 9003-US-PA
Application No.: 10/709,008

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Applicant : Chang
Application No. : 10/709,008
Filed : April 7, 2004
For : METHOD OF FABRICATING A POLYSILICON THIN
FILM
Examiner :
Art Unit : 2812

INFORMATION DISCLOSURE STATEMENT

ASSISTANT COMMISSIONER FOR PATENTS
Arlington, VA22202

Enclosed is a PTO Form 1449 listing 3 reference(s), copy of which is attached. Applicant submits the reference(s) in compliance with his duty of disclosure pursuant to 37 CFR § 1.56 and 1.97. The Examiner is requested to make the citation(s) of official record.

This IDS is being submitted before the first Office Action. Thus, it is believed no fee is due.

The submission of the reference(s) should not be interpreted as admitting them as prior art.

Respectfully Submitted,
JIANQ CHYUN Intellectual Property Office

Date: August 3, 2004

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICATION		ATTY. DOCKET NO.:9003-US-PA	APPLICATION NO.: 10/709,008
		APPLICANT: Chang	
		FILING DATE: April 7, 2004	GROUP 2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIILING DATE (IF APPROPRIATE)
	2002/0115245	2002/08/22	Chang et al.	438	166	2001/02/21

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FIILING DATE (IF APPROPRIATE)

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	Brotherton et al., Excimer-Laser-Annealed Poly-Si Thin-Film Transistors in <i>IEEE Transactions On Electron Devices</i> , Vol. 40, No. 2, pp. 407-413, February 1993.
	Zeng et al. , A Novel Two-Step Laser Crystallization Technique for Low- Temperature Poly-Si TFTs in <i>IEEE Transactions On Electron Devices</i> , Vol. 48, No. 5, pp. 1008-1010, May 2001.

EXAMINER	DATE CONSIDERED

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.